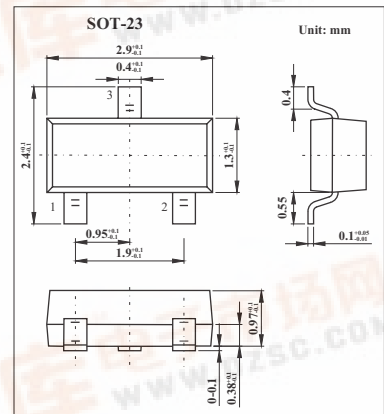


SMD Type Diodes

Silicon Switching Diode  
BAR74

■ Features

- For high-speed switching applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V <sub>R</sub>	50	V
Peak reverse voltage	V <sub>RM</sub>	50	V
Forward current	I <sub>F</sub>	250	mA
Surge forward current, T = 1 μs	I <sub>FS</sub>	4.5	A
Total power dissipation, T <sub>s</sub> = 54 °C	P <sub>tot</sub>	370	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C
Junction ambient (Note 1)	R <sub>th JA</sub>	≤ 330	K/W
Junction soldering point	R <sub>th JS</sub>	≤ 260	K/W

Note

1. Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm<sup>2</sup> Cu.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V <sub>R</sub>	I <sub>R</sub> = 100 μA	50			V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 100 mA			1	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 50 V			0.1	μA
		V <sub>R</sub> = 50 V, T <sub>a</sub> = 150 °C			100	
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> = 0 V, f = 1 MHz			2	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> = 10 mA, R <sub>L</sub> = 100 Ω, measured at I <sub>R</sub> = 1 mA			4	ns

■ Marking

Marking	JBs
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